Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	193	FROHLICH-HANS-GEORG-.in. FROHLICH-H-G-.in. GENZ-O-.in. GENZ-OLIVER-.in. GRAF-WERNER-.in. GRAF-WERNER-DR-.in. GRAF-WERNER-FRANZ-.in. GRAF-WERNER-J-.in. GRUSS-S-.in. GRUSS-STEFAN-.in. HANDKE-M-.in. HANDKE-MATTHIAS-.in. HANDKE-M-A-.in. HEGER-P-.in. HEGER-PERCY-.in. HEINECK-L-.in. HEINECK-LARS-PETER-.in. HEINECK-L-P-.in. LAESSIG-A-.in. LAESSIG-ANTJE-.in. REB-A-.in. REB-ALEXANDER-.in. SCHUPKE-K-.in. SCHUPKE-KIRSTIN-.in. SCHUPKE-KRISTIN-.in. STAVREV-M-.in. STAVREV-MOMTCHIL-.in. VOGT-MIRKO-.in. VOGT-MIRKO-DR-.in. VOGT-M-A-.in.	US-PGPUB; USPAT	OR	ON	2005/08/29 14:35
L2	295	FROHLICH-HANS-GEORG-.in. FROHLICH-H-G-.in. GENZ-O-.in. GENZ-OLIVER-.in. GRAF-WERNER-.in. GRAF-WERNER-DR-.in. GRAF-WERNER-FRANZ-.in. GRAF-WERNER-J-.in. GRUSS-S-.in. GRUSS-STEFAN-.in. HANDKE-M-.in. HANDKE-MATTHIAS-.in. HANDKE-M-A-.in. HEGER-P-.in. HEGER-PERCY-.in. HEINECK-L-.in. HEINECK-LARS-PETER-.in. HEINECK-L-P-.in. LAESSIG-A-.in. LAESSIG-ANTJE-.in. REB-A-.in. REB-ALEXANDER-.in. SCHUPKE-K-.in. SCHUPKE-KIRSTIN-.in. SCHUPKE-KRISTIN-.in. STAVREV-M-.in. STAVREV-MOMTCHIL-.in. VOGT-MIRKO-.in. VOGT-MIRKO-DR-.in. VOGT-M-A-.in.	EPO; JPO; DERWENT	OR	ON	2005/08/29 14:38
L3	71674	contact adj hole	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:38
L4	153633	memory adj (module cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:38
L5	18	L2 and (L3 L4)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:38

L6	477859	(insulator insulating (silicon adj (oxide dioxide))) near2 (layer film coating)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:39
L7	90743	(sacrificial polysilicon poly-silicon poly-si (poly adj (si silicon))) near2 (layer film coating)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:39
L8	149039	(BPSG! glass vitreous) near2 (layer film coating)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:39
L9	16391	(material resist photoresist hard adj mask) near2 plug	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:51
L10	14	L6 same L7 same L8 same L9	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:40
L11	16725	L7 near2 first!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:41
L12	15176	L7 near2 second!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:41
L13	56	L6 and L11 and L12 and L8 and L9	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:41
L14	387	L6 and L7 and L8 and L9	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:41
L15	12	L14 and doping and (liner adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:41
L16	135230	silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:42
L17	6444	liner near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:42

L18	14	L16 same L17 same doping	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:42
L19	46185	(arc! near (layer film coating)) antireflective antireflection anti-reflective anti-reflection anti adj reflective anti adj reflection	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:42
L20	12230	hard adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:42
L21	510107	resist photoresist photo-resist	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:42
L22	23	L19 with L20 with L21 with both	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:43
L23	45	L19 with filling near2 material	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/29 14:43
L25	1496492	electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 14:47
L26	562062	plug	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 14:47
L27	3	(25 and 26 and 7 and 8 and 9).clm.	US-PGPUB	OR	ON	2005/08/29 14:50
L28	0	(7 with 8 with 9).clm.	US-PGPUB	OR	ON	2005/08/29 14:52
L29	828480	resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 14:52
L30	3	(7 with 8 with 29).clm.	US-PGPUB	OR	ON	2005/08/29 14:52